1. Scope :

This specification applies to PIN silicon photodiode chips,
Device No. PD-30165-B.

2. Structure :

2-1. Type : PIN diode.
2-2. Electrodes :
Top side (Anode) : Aluminum alloy .
Back side (Cathode) : Gold alloy.

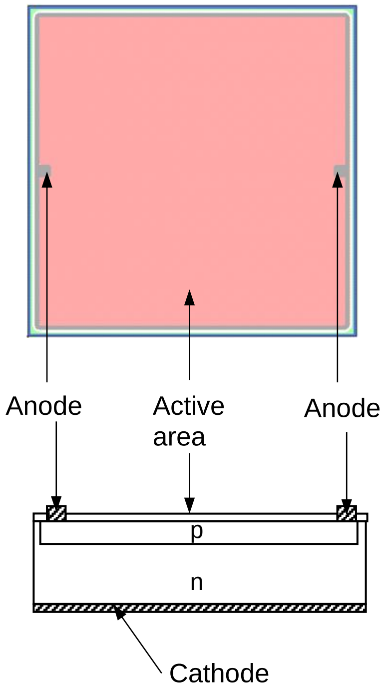
3. Size :

3-1. Chip size(Including scribe lane) : 165.35 mil × 165.35 mil (4.200 mm × 4.200 mm).
3-2. Chip thickness : 12 ±1.5 mil (0.305 ± 0.038mm).
3-3. Active area : 154.49 mil × 154.49 mil (3.924 mm × 3.924 mm).
3-4. Bonding pad (Anode) : 5.83 mil x 5.91mil (0.148 mm x 0.150mm).
3-5. Pattern drawing : Refer to the attached drawing.

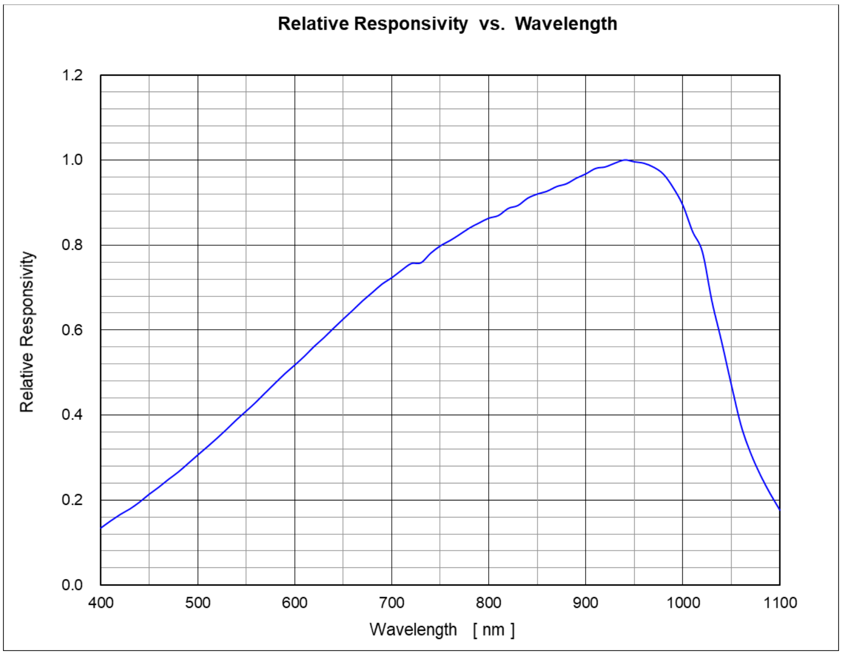
4. Electro-optical characteristics (Ta = 25 ℃)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
※Reverse dark current	I_D	V_R=10V Ee=0mW/cm^2			30	nA
※Reverse breakdown voltage	$V_{(BR)R}$	I_R=100uA Ee=0mW/cm^2	33			V
Reverse light current	I_L	V_R =5V T=2856K Ee=5mW/cm^2		170		μA
Total Capacitance	C_t	V_R =5V Ee=0mW/cm^2 f=1MHz		36		pF

※Based on 100% probing



5. Relative spectral responsivity



※Bare chip measured with integrating sphere, for reference only.